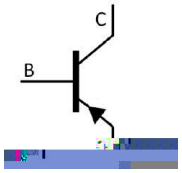
Silicon PNP transistor in a TO-92LM Plastic Package.

Complementary pair with 2SD788.

Low frequency power amplifier.



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} ClassificatiDToMaking

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-20	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current (DC)	I_C	-2.0	A
Collector Power Dissipation	P_C	0.9	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

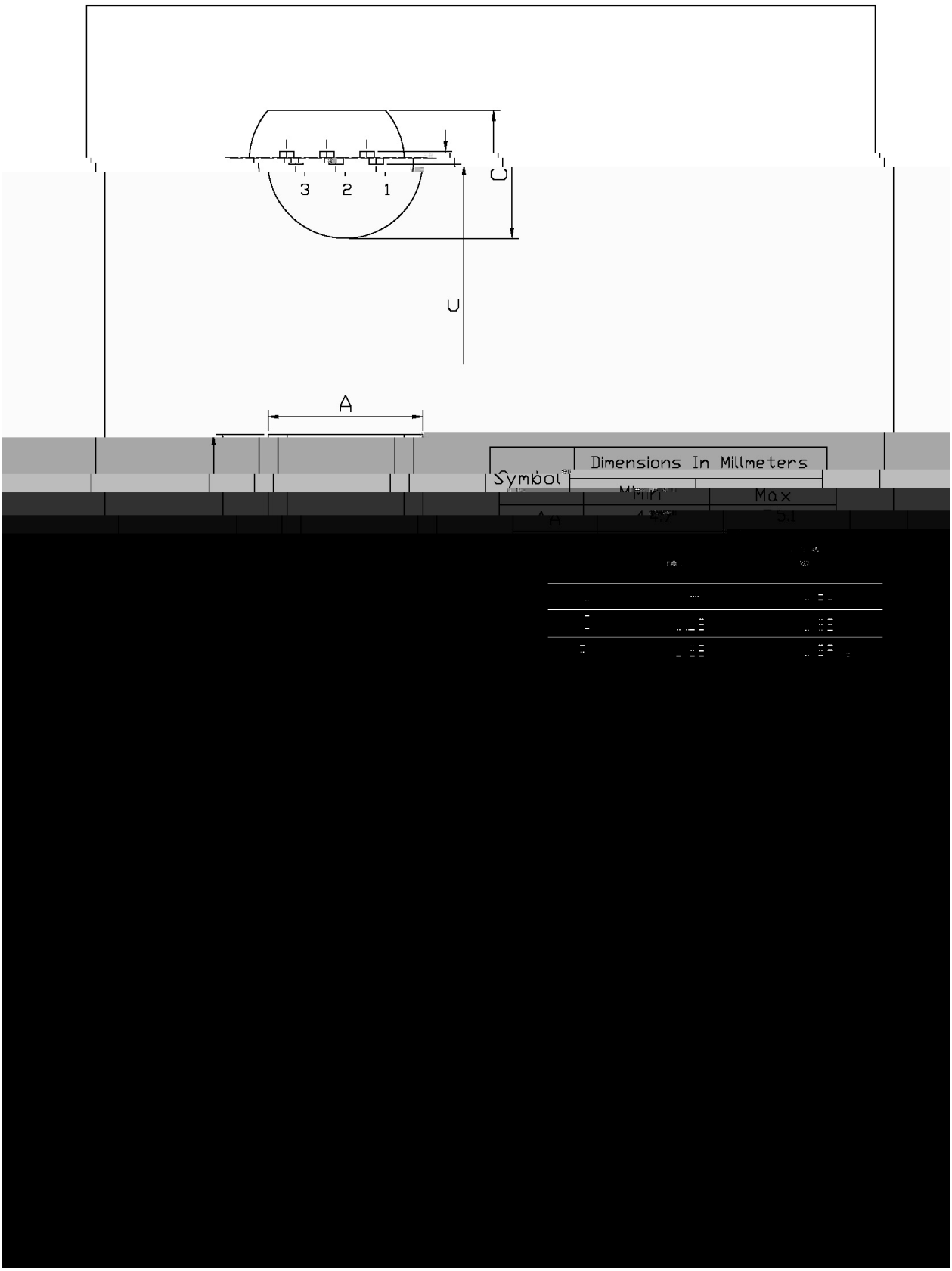
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10μA I_E=0	-20			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA R_{BE}=∞	-20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-10μA I_C=0	-6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-16V I_E=0			-2.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.2	μA
DC Current Gain	h_{FE}	V_{CE}=-2.0V I_C=-0.1A	100		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1.0A I_B=-0.1A			-0.3	V
Transition Frequency	f_T	V_{CE}=-2.0V I_C=-10mA		150		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		50		pF

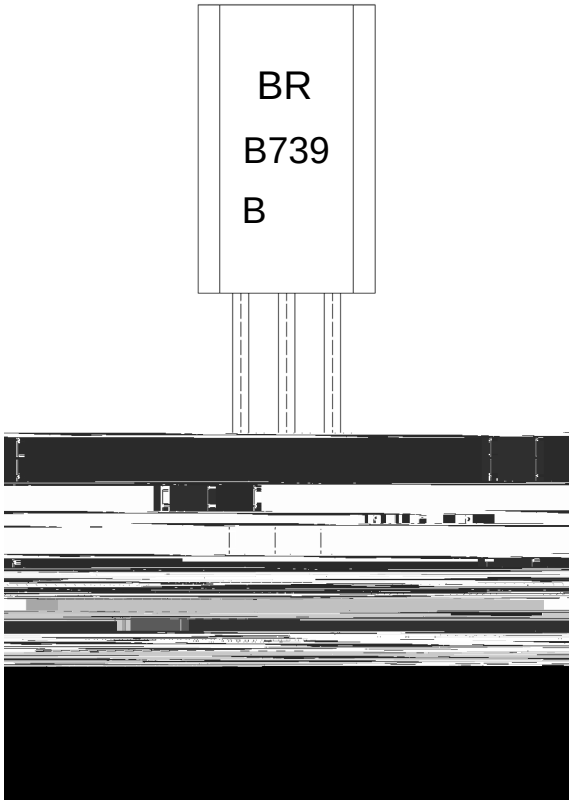
2SB739

/ Package Dimensions

TO-92LM Unit: mm



/ Marking Instruct/9.M



Note:

BR:	Company Code.
B739:	Product Type.
B:	h_{FE} Classificat/9.M Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)

1 25 150 60 90sec;	Note: 1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5	10 1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension	(unit mm3)